

Document No.	853-0146
ECN No.	86487
Date of Issue	November 11, 1986
Status	Product Specification
Memory Products	

# 82S183

## 8K-bit TTL bipolar PROM

### DESCRIPTION

The 82S183 is field programmable, which means that custom patterns are immediately available by following the Signetics Generic fusing procedure. The standard 82S183 is supplied with all outputs at logical Low. Outputs are programmed to a logic High level at any specified address by fusing the Ni-Cr link matrix.

This device includes on-chip decoding and 3 Chip Enable inputs for ease of memory expansion. It features 3-State outputs for optimization of word expansion in bused organizations.

In the Transparent Read mode, stored data is addressed by applying a binary code to the address inputs while holding Strobe High. In this mode the output drivers are controlled solely by CE1, CE2, and CE3 lines

A D-type latch is used to enable the 3-State output drivers. In the Latched Read mode, outputs are held in their previous state (High, Low, or Hi-Z) as long as Strobe is Low, regardless of the state of Address or Chip Enable. A positive Strobe transition causes data from the applied address to reach the outputs if the chip is enabled, and causes outputs to go to the Hi-Z state if the chip is disabled.

A negative Strobe transition causes outputs to be locked into their last Read Data condition if the chip was enabled, or causes outputs to be locked into the Hi-Z condition if the chip was disabled.

Ordering information can be found on the following page.

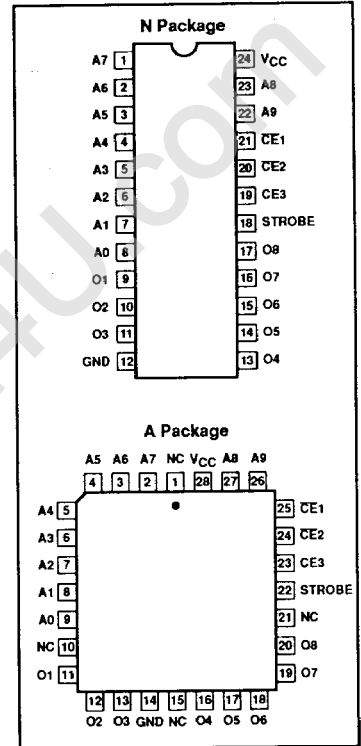
### FEATURES

- Address access time: 60ns max
- Power dissipation: 80μW/bit typ
- Input loading: -100μA max
- On-chip address decoding
- No separate fusing pins
- Unprogrammed outputs are Low level
- Fully TTL compatible
- Three Chip Enable inputs
- Outputs: 3-State

### APPLICATIONS

- Sequential controllers
- Microprogramming
- Hardwired algorithms
- Control store
- Code conversion

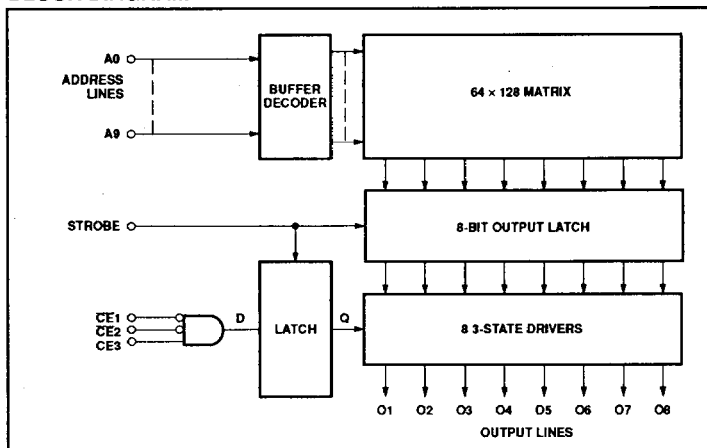
### PIN CONFIGURATIONS



# 8K-bit TTL bipolar PROM (1024 × 8)

82S183

## BLOCK DIAGRAM



## ORDERING INFORMATION

DESCRIPTION	ORDER CODE
24-Pin Plastic Dual-In-Line 600mil-wide	N82S183 N
28-Pin Plastic Leaded Chip Carrier 450mil-square	N82S183 A

## ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CC</sub>	Supply voltage	+7.0	V <sub>DC</sub>
V <sub>IN</sub>	Input voltage	+5.5	V <sub>DC</sub>
V <sub>O</sub>	Output voltage Off-State	+5.5	V <sub>DC</sub>
T <sub>amb</sub>	Operating temperature range	0 to +75	°C
T <sub>stg</sub>	Storage temperature range	-65 to +150	°C

## 8K-bit TTL bipolar PROM (1024 × 8)

82S183

## DC ELECTRICAL CHARACTERISTICS

 $0^{\circ}\text{C} \leq T_{\text{amb}} \leq +75^{\circ}\text{C}$ ,  $4.75\text{V} \leq V_{\text{CC}} \leq 5.25\text{V}$ 

SYMBOL	PARAMETER	TEST CONDITIONS <sup>1,2</sup>	LIMITS			UNIT	
			Min	Typ <sup>3</sup>	Max		
<b>Input voltage<sup>2</sup></b>							
$V_{\text{IL}}$	Low	$I_{\text{IN}} = -12\text{mA}$	2.0		0.8	V	
$V_{\text{IH}}$	High					V	
$V_{\text{IC}}$	Clamp					V	
<b>Output voltage<sup>2</sup></b>							
$V_{\text{OL}}$	Low	$\overline{\text{CE}}_{1,2} = \text{Low}, \text{CE}_3 = \text{High}$ $I_{\text{OUT}} = 9.6\text{mA}$	2.4		0.45	V	
$V_{\text{OH}}$	High	$I_{\text{OUT}} = -2.0\text{mA}$				V	
<b>Input current<sup>1</sup></b>							
$I_{\text{IL}}$	Low	$V_{\text{IN}} = 0.45\text{V}$	25		-100	$\mu\text{A}$	
$I_{\text{IH}}$	High	$V_{\text{IN}} = 5.5\text{V}$				25	$\mu\text{A}$
<b>Output current</b>							
$I_{\text{OZ}}$	Hi-Z state	$\overline{\text{CE}} = \text{High}, \text{CE} = \text{Low}, V_{\text{OUT}} = 5.5\text{V}$ $\overline{\text{CE}} = \text{High}, \text{CE} = \text{Low}, V_{\text{OUT}} = 0.5\text{V}$	-15		40	$\mu\text{A}$	
$I_{\text{OS}}$	Short circuit <sup>4</sup>	$\overline{\text{CE}} = \text{Low}, \text{CE} = \text{High}, V_{\text{OUT}} = 0\text{V}$				-40	$\mu\text{A}$
		High stored				-70	$\text{mA}$
<b>Supply current<sup>5</sup></b>							
$I_{\text{CC}}$		$V_{\text{CC}} = 5.25\text{V}$		130	175	$\text{mA}$	
<b>Capacitance</b>							
$C_{\text{IN}}$	Input	$\overline{\text{CE}}_{1,2} = \text{High}, \text{CE}_3 = \text{Low}, V_{\text{CC}} = 5.0\text{V}$ $V_{\text{IN}} = 2.0\text{V}$		5		$\text{pF}$	
$C_{\text{OUT}}$	Output	$V_{\text{OUT}} = 2.0\text{V}$		8		$\text{pF}$	

## NOTES:

- Positive current is defined as into the terminal referenced.
- Typical values are at  $V_{\text{CC}} = 5\text{V}$ ,  $T_{\text{amb}} = +25^{\circ}\text{C}$ .
- No more than one output should be grounded at the same time and Strobe should be disabled. Strobe is in High state.
- Measured with all inputs grounded and all outputs open.

# 8K-bit TTL bipolar PROM (1024 × 8)

82S183

## AC ELECTRICAL CHARACTERISTICS

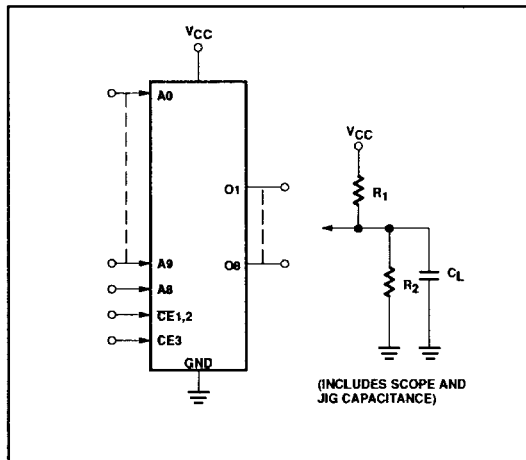
$R_1 = 470\Omega$ ,  $R_2 = 1k\Omega$ ,  $C_L = 30pF$ ,  $0^\circ C \leq T_{amb} \leq +75^\circ C$ ,  $4.75V \leq V_{CC} \leq 5.25V$

SYMBOL	PARAMETER	TO	FROM	TEST CONDITIONS	LIMITS			UNIT
					Min	Typ <sup>2</sup>	Max	
<b>Access time<sup>1</sup></b>								
$t_{AA}$		Output	Address	Latched or transparent read		45	60	ns
$t_{CE}$		Output	Chip Enable			25	40	ns
<b>Disable time<sup>1,4</sup></b>								
$t_{CD}$		Output	Chip Disable	Latched or transparent read		25	40	ns
<b>Setup and hold time<sup>3</sup></b>								
$t_{CDS}$	Setup time	Output	Chip Enable	Latched read only	40			ns
$t_{CDH}$	Hold time	Output	Chip Enable		10			ns
$t_{ADH}$	Hold time	Output	Address	Latched or transparent read	0			ns
<b>Pulse width<sup>3</sup></b>								
$t_{SW}$	Strobe			Latched read only	30	15		ns
<b>Latch time<sup>3</sup></b>								
$t_{SL}$	Strobe			Latched read only	60	35		ns
<b>Delatch time<sup>3,4</sup></b>								
$t_{DL}$	Strobe			Latched read only			30	ns

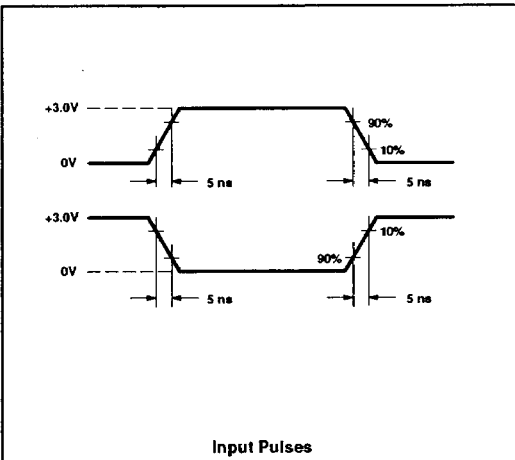
**NOTES:**

1. If the Strobe is High, the device functions in a manner identical to conventional bipolar ROMs. The timing diagram shows valid data will appear  $t_{AA}$  nanoseconds after the address has changed  $t_{CE}$  nanoseconds after the output circuit is enabled.  $t_{CD}$  is the time required to disable the output and switch it to an off or High impedance state after it has been enabled.
2. Typical values are  $V_{CC} = 5V$ ,  $T_{amb} = +25^\circ C$ .
3. In latched Read Mode data from any selected address will be held on the output when Strobe is lowered. Only when Strobe is raised will new location data be transferred and Chip Enable conditions be stored. The new data will appear on the output if the Chip Enable conditions enable the outputs.
4. Measured at a delta of 0.5V from Logic Level with  $R_1 = 750\Omega$ ,  $R_2 = 750\Omega$  and  $C_L = 5pF$ .
5. All AC parameters are measured at 1.5V unless otherwise specified.

### TEST LOAD CIRCUIT



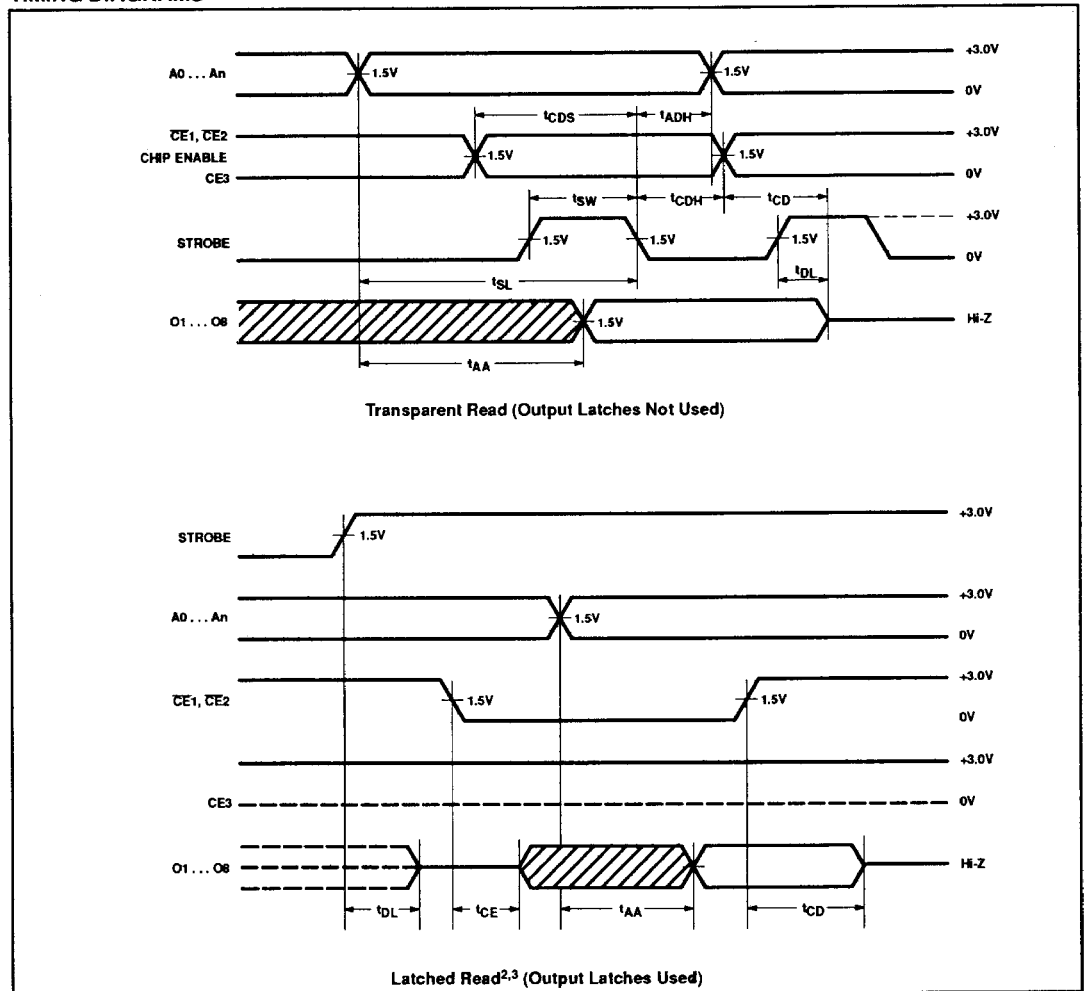
### VOLTAGE WAVEFORM



# 8K-bit TTL bipolar PROM (1024 × 8)

82S183

## TIMING DIAGRAMS<sup>1</sup>



**NOTES:**

1. All AC parameters are measured at 1.5V unless otherwise specified.
2. In Latched Read Mode data from any selected address will be held on the output when Strobe is lowered. Only when Strobe is raised will new location data be transferred and Chip Enable conditions be stored. The new data will appear on the output if the Chip Enable conditions enable the outputs.
3. Areas shown by crosshatch are latched data from previous address.